AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A point emission type light emitting element comprising:

a stripe ridge having an n-type layer, an active layer and a p-type layer that are formed from semiconductors on a substrate, so as to emit light from one end face of the stripe ridge,

wherein the stripe ridge has a protruding portion on the end face and the surface of the light emitting element is covered with a shading film except for the tip of the protruding portion, and

wherein the shading film comprises a material selected from the group consisting of ~~comprising~~ Cr/Ni, Cr, Ti/Pt, Ti, Ni, Al, Ag and Au.

2. (Previously Presented) The point emission type light emitting element according to claim 1, wherein said n-type layer, said active layer and said p-type layer comprise nitride semiconductor.

Claims 3-11 (Canceled).

12. (Previously Presented) The point emission type light emitting element according to claim 1, wherein the width of the stripe ridge is in a range from 1μm to 100μm.

13. (Previously Presented) The point emission type light emitting element according to claim 1, wherein the width of the protruding portion is in a range from 1μm to 10μm.

14. (Currently Amended) A point emission type light emitting element comprising:

a stripe ridge having an n-type layer, an active layer and a p-type layer that are formed from semiconductors on a substrate, so as to emit light from one end face of the stripe ridge,

wherein the stripe ridge has a protruding portion on the end face and the surface of the light emitting element is covered with a shading film except for the tip of the protruding portion, and ~~The point emission type light emitting element according to claim 1,~~

wherein the shading film comprises ~~a material selected from the group consisting of Cr/Ni, TiO_2, SiO_2, Cr, Ti/Pt, Ti, Ni, Al, Ag and Au~~.

15. (Previously Presented) The point emission type light emitting element according to claim 1, wherein the ridge stripe is formed by etching to a depth that does not reach the active layer and the protruding portion is formed by etching to a depth that reaches the n-type layer.

16. (New) The point emission type light emitting element according to claim 14, wherein said n-type layer, said active layer and said p-type layer comprise nitride semiconductor.

17. (New) The point emission type light emitting element according to claim 14, wherein the width of the stripe ridge is in a range from 1μm to 100μm.

18. (New) The point emission type light emitting element according to claim 14, wherein the width of the protruding portion is in a range from 1μm to 10μm.

19. (New) The point emission type light emitting element according to claim 14, wherein the ridge stripe is formed by etching to a depth that does not reach the active layer and the protruding portion is formed by etching to a depth that reaches the n-type layer.